

STPSC806D

600 V power Schottky silicon carbide diode

Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Particularly suitable in PFC boost diode function

Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide bandgap material allows the design of a Schottky diode structure with a 600 V rating. Due to the Schottky construction no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

ST SiC diodes will boost the performance of PFC operations in hard switching conditions.

Obsolete Product(s)

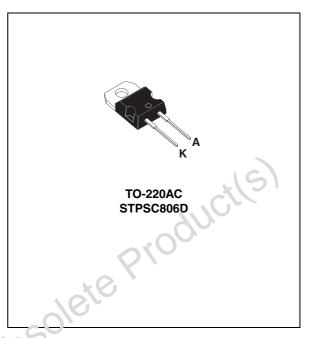


Table 1. Device summary

I _{F(AV)}	8 A
V_{RRM}	600 V
T _{j (max)}	175 °C
Q _{C (typ)}	10 nC

Characteristics STPSC806D

1 Characteristics

Table 2. Absolute ratings (limiting values at 25 °C unless otherwise specified)

Symbol	Paramet	Value	Unit	
V_{RRM}	Repetitive peak reverse voltage	600	٧	
I _{F(RMS)}	RMS forward current	18	Α	
I _F	Continuous forward current	T _C = 115 °C	8	Α
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal	30	Α
I _{FRM}	Repetitive peak forward current	$\delta = 0.1$, $T_C = 110$ °C, $T_j = 150$ °C	30	А
T _{stg}	Storage temperature range	-55 to +175	°C	
T _j	Operating junction temperature	-40 to +175	°C	

Table 3. Thermal resistance

Symbol	Parameter	Maximum Value	Unit
R _{th(j-c)}	Junction to case	2.4	°C/W

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Tests conditions		Min.	Тур	Max.	Unit
I _R ⁽¹⁾	Reverse leakage	T _j = 25 °C	V - V	2.	20	100	μA
^{IR} current	T _j = 150 °C	$V_R = V_{RRM}$		150	1000	μΑ	
V _F ⁽²⁾	Forward voltage drop	T _j = 25 °C	Τ- Ο Λ		1.4	1.7	V
VF V Troiward voltage drop	T _j = 150 °C	I _F = 8 A		1.6	2.1	V	

^{1.} $t_p = 10 \text{ ms}, \ \delta < 2\%$

To evaluate the conduction losses use the following equation:

 $P = 1.2 \times I_{F(AV)} + 0.113 \times I_{F^{2}(RMS)}$

Table 5. Other parameters

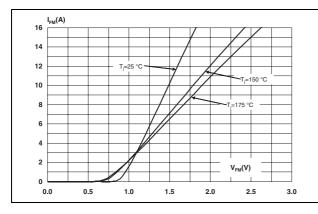
Symbol Parameter		Parameter	Test conditions	Тур	Unit
\ (Q _c	Total capacitive charge	$V_r = 400 \text{ V}, I_F = 8 \text{ A } dI_F/dt = -200 \text{ A/}\mu\text{s}$ $T_j = 150 \text{ °C}$	10	nC
cO/ϵ	C	Total capacitance	$V_r = 0 \text{ V}, T_c = 25 \text{ °C}, F = 1 \text{ Mhz}$	450	pF
Open					

^{2.} $t_p = 500 \ \mu s, \ \delta < 2\%$

STPSC806D Characteristics

Figure 1. Forward voltage drop versus forward current (typical values)

Figure 2. Reverse leakage current versus reverse voltage applied (maximum values)



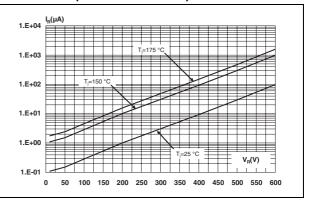
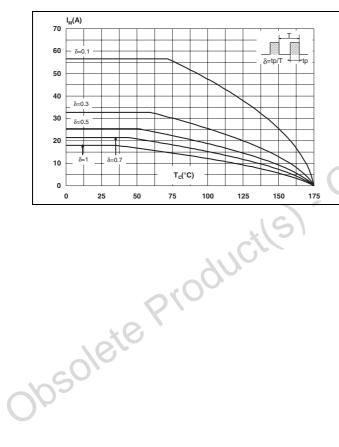
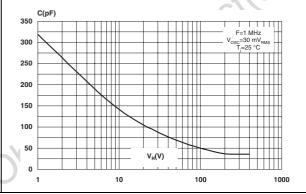


Figure 3. Peak forward current versus case temperature

Figure 4. Junction capacitance versus reverse voltage applied (typical values)



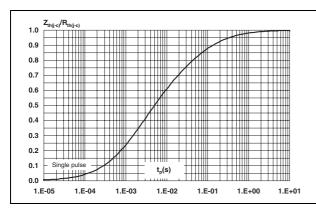


577

Characteristics STPSC806D

Figure 5. Relative variation of thermal impedance junction to case versus pulse duration

Figure 6. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform, typical values)



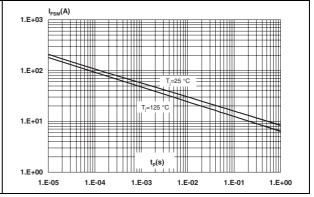
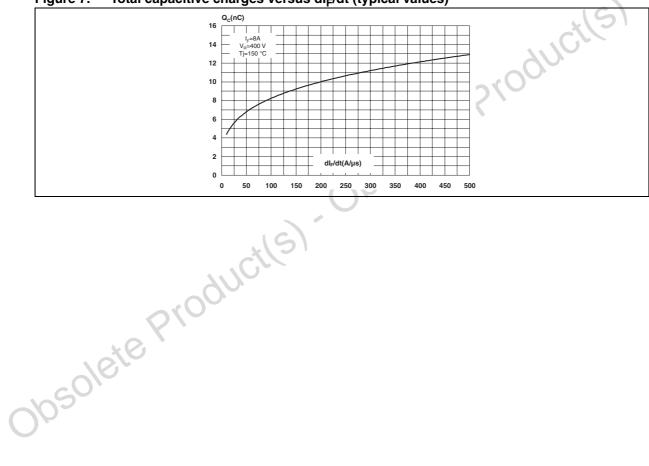


Figure 7. Total capacitive charges versus dl_E/dt (typical values)



4/7

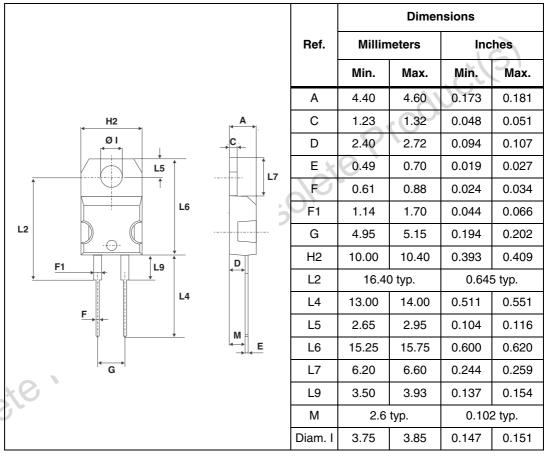
STPSC806D Package information

2 Package information

- Epoxy meets UL94, V0
- Cooling method: C
- Recommended torque value: 0.4 to 0.6 N⋅m

In order to meet environmental requirements, ST offers these devices in ECOPACK[®] packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at www.st.com.

Table 6. TO-220AC Dimensions



577

Ordering information STPSC806D

3 Ordering information

Table 7. Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPSC806D	STPSC806D	TO-220AC	1.86 g	50	Tube

4 Revision history

Table 8. Document revision history

Table 8.	Document rev	ision history
Date	Revision	Description of Changes
05-May-2008	1	First issue
05-May-2008	1	Description of Changes First issue
		Cities and the cities are the cities and the cities are the cities and the cities are the cities
		2,000
		1018
		-150
		OA
		1
	.(5)
	(C).	
	90,	
20	9	
C.Y.		
10th		
110		

6/7

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2008 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

